

What is claimed is:

- 1        1.    A method comprising:  
2                forming a source drain extension by implanting  
3    boron, carbon, and fluorine.
- 1        2.    The method of claim 1 including implanting carbon  
2    to a depth deeper than the boron implant.
- 1        3.    The method of claim 2 including implanting  
2    fluorine to a depth deeper than the boron implant.
- 1        4.    The method of claim 1 including implanting carbon  
2    at an energy of about 6 KeV.
- 1        5.    The method of claim 4 including implanting carbon  
2    at a dose of about  $1E15$  atoms/cm<sup>2</sup>.
- 1        6.    The method of claim 1 including performing a Halo  
2    implant before the implanting boron.
- 1        7.    A method comprising:  
2                implanting boron and fluorine to form a source  
3    drain extension; and  
4                implanting an additional species to reduce  
5    transient enhanced diffusion of boron.

1        8.    The method of claim 7 including implanting carbon  
2    as said additional species.

1        9.    The method of claim 8 including implanting carbon  
2    to a depth deeper than the boron implant.

1        10.   The method of claim 9 including implanting  
2    fluorine to a depth deeper than the boron implant.

1        11.   The method of claim 8 including implanting carbon  
2    at an energy of about 6 KeV.

1        12.   The method of claim 11 including implanting  
2    carbon at a dose of about  $1E15$  atoms/cm<sup>2</sup>.

1        13.   The method of claim 7 including performing a Halo  
2    implant before implanting boron.

1        14.   An integrated circuit comprising:  
2                a P-type transistor having a source drain  
3    extension including carbon and boron.

1        15.   The circuit of claim 14 wherein said extension  
2    includes fluorine.

1           16. The circuit of claim 14 wherein carbon is deeper  
2 than said boron.

3           17. The circuit of claim 14 wherein fluorine is  
4 deeper than said boron.

1           18. A method comprising:  
2                 performing an Arsenic Halo implant before  
3 implanting to form P-type source/drain extensions.

1           19. The method of claim 18 including forming the P-  
2 type source/drain extensions using boron, carbon, and  
3 fluorine implants.

1           20. The method of claim 18 including implanting  
2 carbon to a depth deeper than the boron implant.

1           21. The method of claim 20 including implanting  
2 fluorine to a depth deeper than the boron implant.